

DYNAMIC CHARACTERISTICS

APT5015BVFR_SVFR

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C _{iss}	Input Capacitance	V _{GS} = 0V		4400	5280	pF
C _{oss}	Output Capacitance	V _{DS} = 25V		600	840	
C _{rss}	Reverse Transfer Capacitance	f = 1 MHz		230	350	
Q _g	Total Gate Charge ③	V _{GS} = 10V		200	300	nC
Q _{gs}	Gate-Source Charge	V _{DD} = 0.5 V _{DSS}		30	45	
Q _{gd}	Gate-Drain ("Miller") Charge	I _D = I _D [Cont.] @ 25°C		80	120	
t _{d(on)}	Turn-on Delay Time	V _{GS} = 15V		12	25	ns
t _r	Rise Time	V _{DD} = 0.5 V _{DSS}		14	30	
t _{d(off)}	Turn-off Delay Time	I _D = I _D [Cont.] @ 25°C		55	80	
t _f	Fall Time	R _G = 1.6Ω		11	20	

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
I _S	Continuous Source Current (Body Diode)			32	Amps
I _{SM}	Pulsed Source Current ① (Body Diode)			128	
V _{SD}	Diode Forward Voltage ② (V _{GS} = 0V, I _S = -I _D [Cont.])			1.3	Volts
dv/dt	Peak Diode Recovery dv/dt ⑤			15	V/ns
t _{rr}	Reverse Recovery Time (I _S = -I _D [Cont.], di/dt = 100A/μs)	T _j = 25°C		250	ns
		T _j = 125°C		525	
Q _{rr}	Reverse Recovery Charge (I _S = -I _D [Cont.], di/dt = 100A/μs)	T _j = 25°C	1.6		μC
		T _j = 125°C	6.0		
I _{RRM}	Peak Recovery Current (I _S = -I _D [Cont.], di/dt = 100A/μs)	T _j = 25°C	13		Amps
		T _j = 125°C	21		

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
R _{θJC}	Junction to Case			0.34	°C/W
R _{θJA}	Junction to Ambient			40	

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② Pulse Test: Pulse width < 380 μs, Duty Cycle < 2%

③ See MIL-STD-750 Method 3471

④ Starting T_j = +25°C, L = 2.54mH, R_G = 25Ω, Peak I_L = 32A

⑤ I_S = -I_D [Cont.], di/dt = 100A/μs, V_{DD} - V_{DSS}, T_j = 150°C, R_G = 2.0Ω, V_R = 200V.

APT Reserves the right to change, without notice, the specifications and information contained herein.

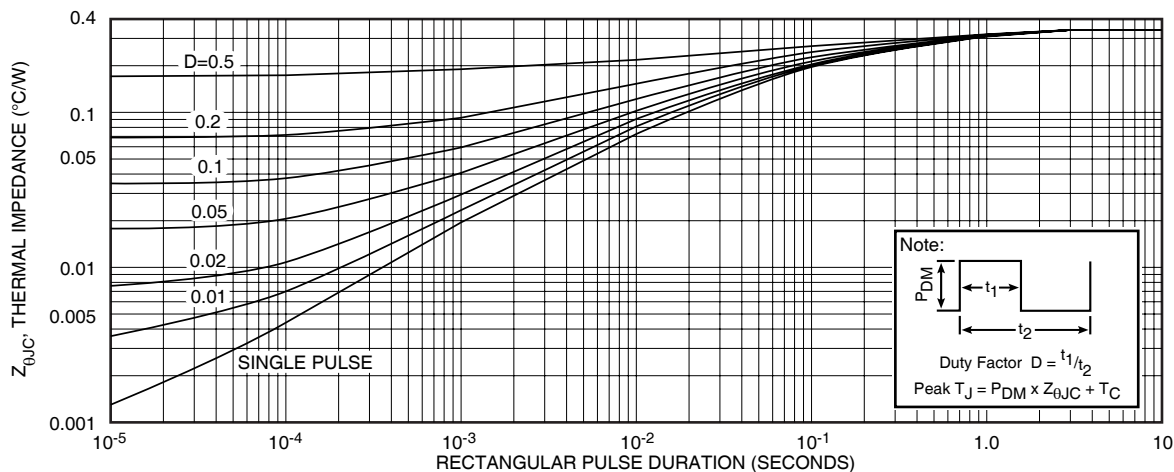


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

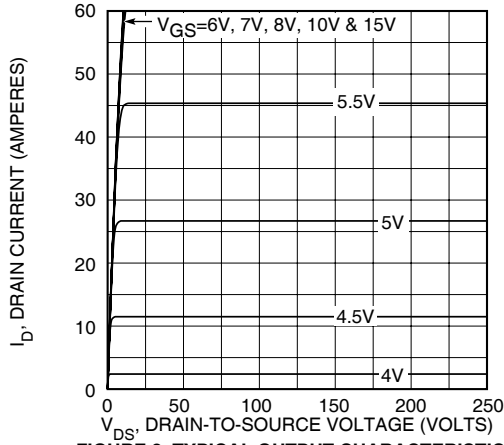


FIGURE 2, TYPICAL OUTPUT CHARACTERISTICS

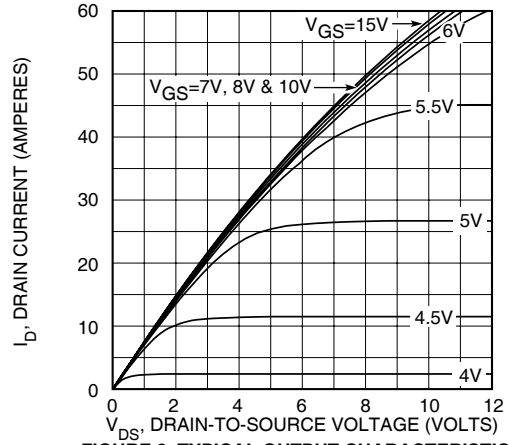


FIGURE 3, TYPICAL OUTPUT CHARACTERISTICS

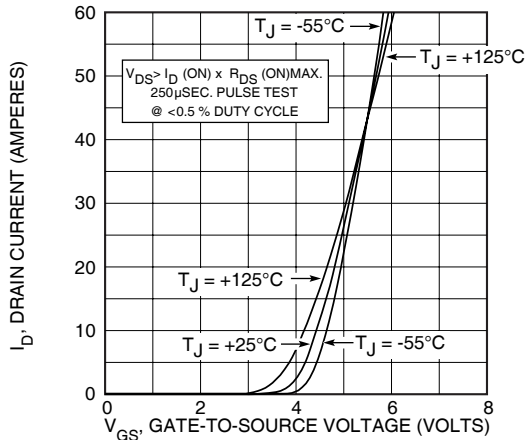


FIGURE 4, TYPICAL TRANSFER CHARACTERISTICS

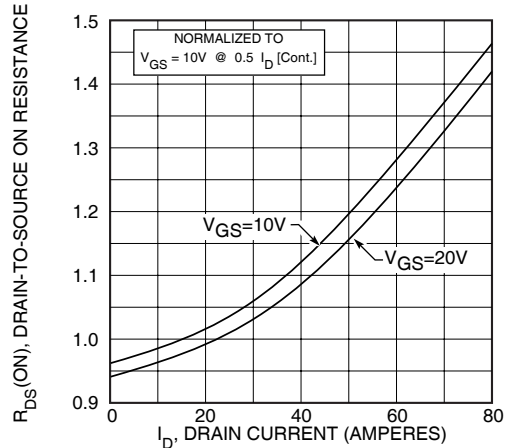


FIGURE 5, $R_{DS(ON)}$ vs DRAIN CURRENT

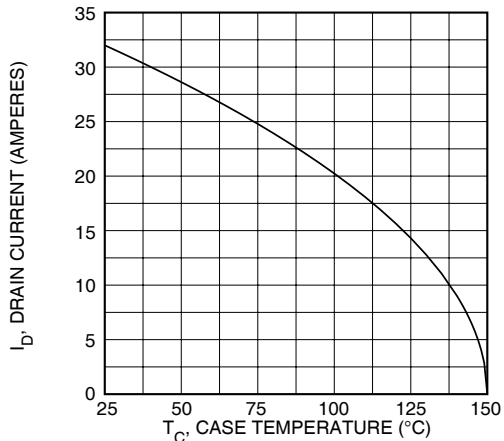


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

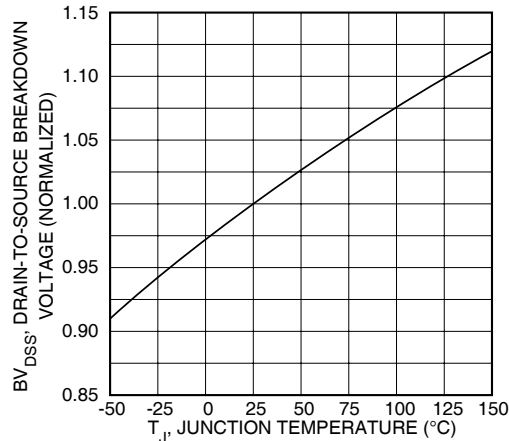


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

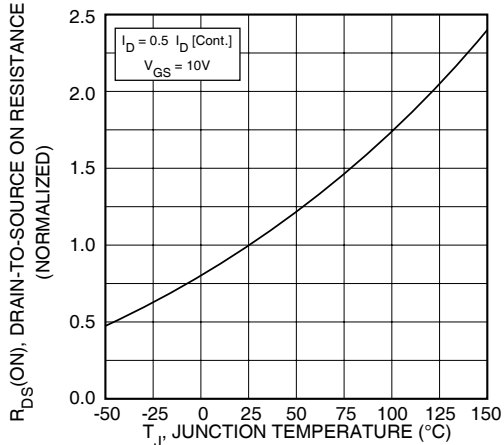


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

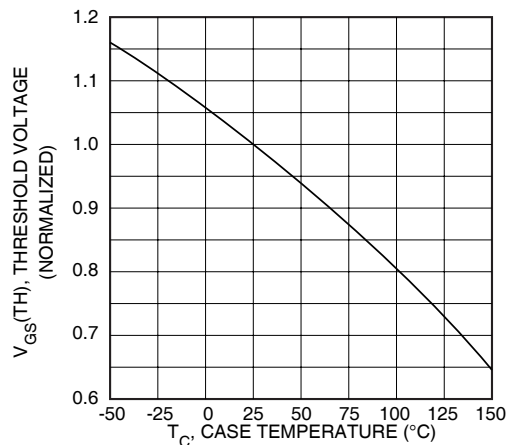


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

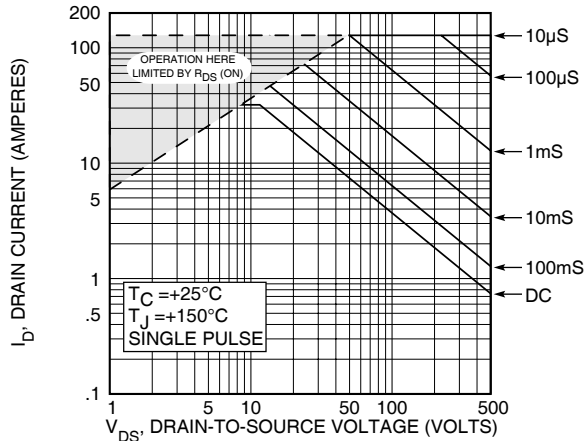


FIGURE 10, MAXIMUM SAFE OPERATING AREA

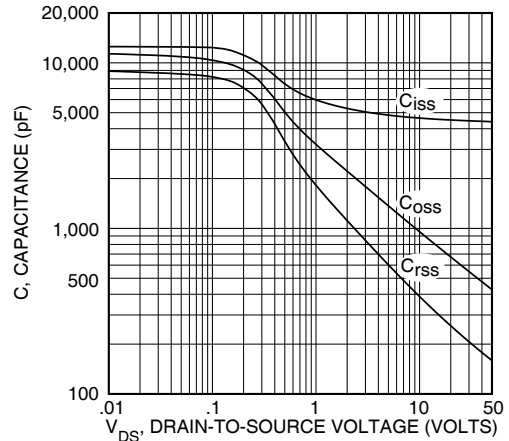


FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

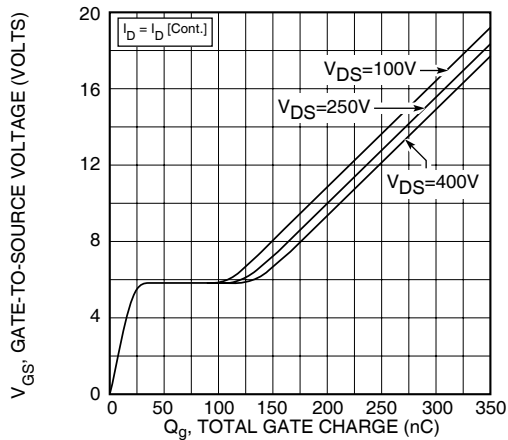


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

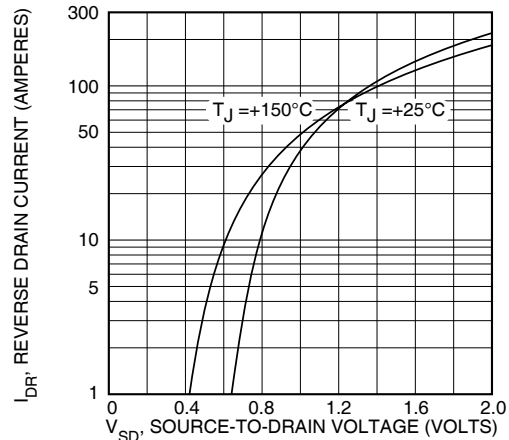
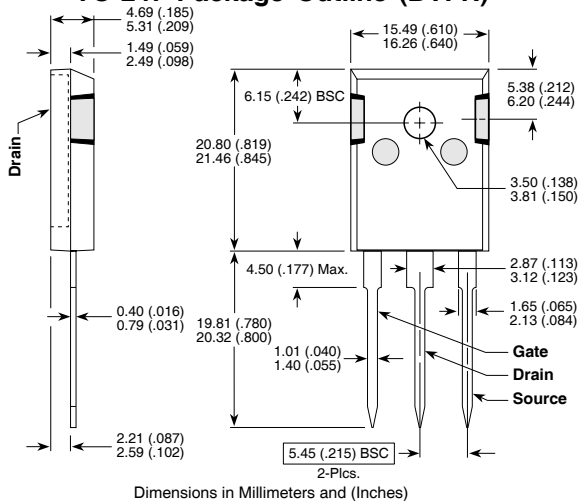


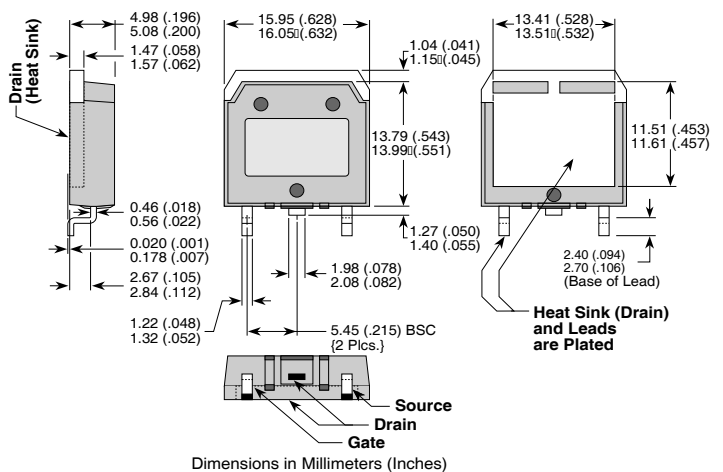
FIGURE 13, TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE

TO-247 Package Outline (BVFR)



Dimensions in Millimeters and (Inches)

D³PAK Package Outline (SVFR)



Dimensions in Millimeters (Inches)

Mouser Electronics

Authorized Distributor

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